



# PBSS4160PANP

60 V, 1 A NPN/PNP low  $V_{CEsat}$  transistor

30 September 2025

Product data sheet

## 1. General description

NPN/PNP low  $V_{CEsat}$  transistor in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package.

NPN/PNP complement: PBSS4160PAN

PNP/PNP complement: PBSS5160PAP

## 2. Features and benefits

- Very low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain  $h_{FE}$  at high  $I_C$
- Reduced Printed-Circuit Board (PCB) requirements
- High efficiency due to less heat generation

## 3. Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

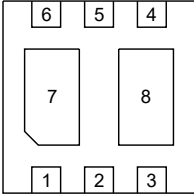
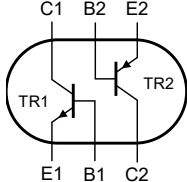
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor; for the PNP transistor with negative polarity</b>						
$V_{CEO}$	collector-emitter voltage	open base	-	-	60	V
$I_C$	collector current		-	-	1	A
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	1.5	A
<b>TR1 (NPN)</b>						
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = 0.5$ A; $I_B = 50$ mA; pulsed; $t_p \leq 300$ $\mu$ s; $\delta \leq 0.02$ ; $T_{amb} = 25$ °C	-	-	240	m $\Omega$
<b>TR2 (PNP)</b>						
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = -0.5$ A; $I_B = -50$ mA; pulsed; $t_p \leq 300$ $\mu$ s; $\delta \leq 0.02$ ; $T_{amb} = 25$ °C	-	-	360	m $\Omega$

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	 <p>Transparent top view DFN2020-6 (SOT1118)</p>	 <p>sym139</p>
2	B1	base TR1		
3	C2	collector TR2		
4	E2	emitter TR2		
5	B2	base TR2		
6	C1	collector TR1		
7	C1	collector TR1		
8	C2	collector TR2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
<a href="#">PBSS4160PANP</a>	DFN2020-6	plastic, leadless thermal enhanced ultra thin small outline package; no leads; 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	<a href="#">SOT1118</a>

7. Marking

Table 4. Marking codes

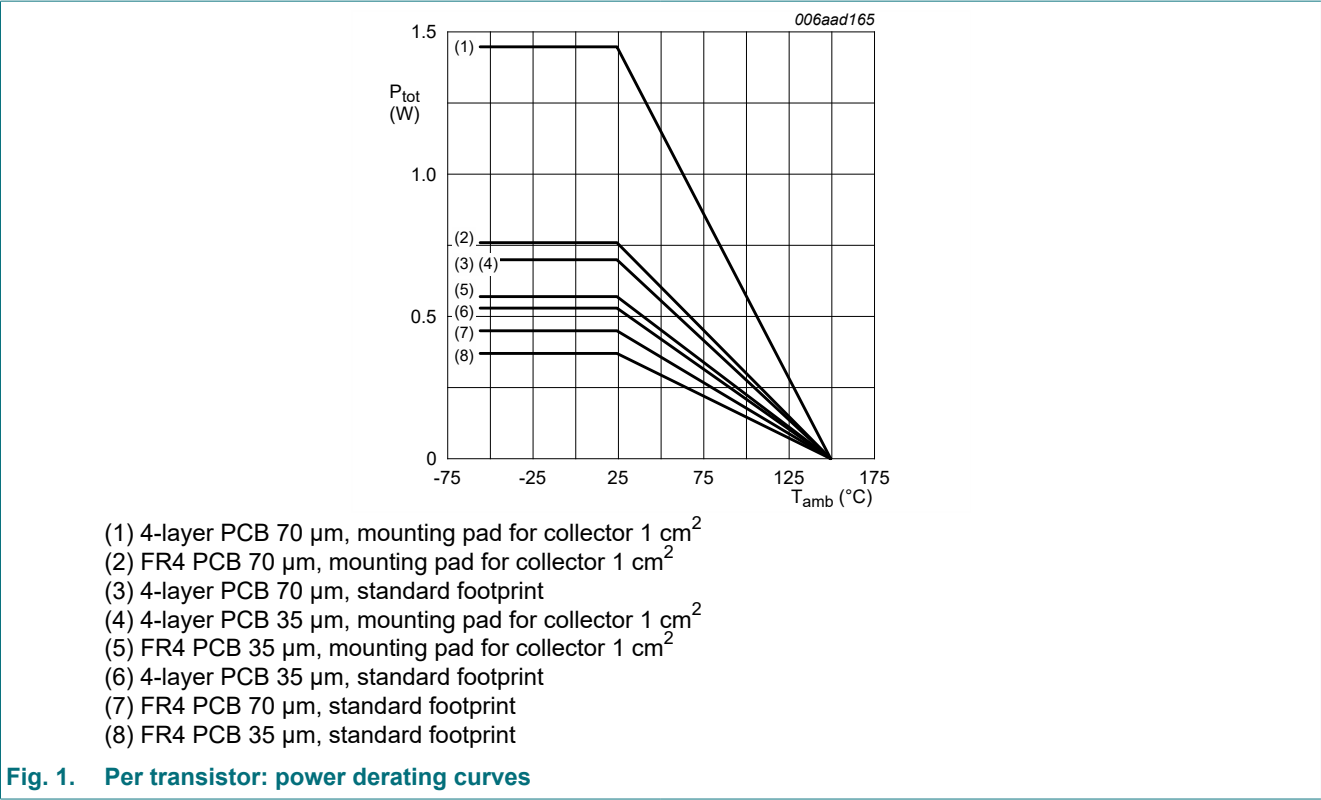
Type number	Marking code
PBSS4160PANP	2M

8. Limiting values

Table 5. Limiting values  
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor; for the PNP transistor with negative polarity						
V <sub>CBO</sub>	collector-base voltage	open emitter		-	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	7	V
I <sub>C</sub>	collector current			-	1	A
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	1.5	A
I <sub>B</sub>	base current			-	0.3	A
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	1	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	370	mW
			[2]	-	570	mW
			[3]	-	530	mW
			[4]	-	700	mW
			[5]	-	450	mW
			[6]	-	760	mW
			[7]	-	700	mW
			[8]	-	1450	mW
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	510	mW
			[2]	-	780	mW
			[3]	-	730	mW
			[4]	-	960	mW
			[5]	-	620	mW
			[6]	-	1040	mW
			[7]	-	960	mW
			[8]	-	2000	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- [6] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	338	K/W
			[2]	-	-	219	K/W
			[3]	-	-	236	K/W
			[4]	-	-	179	K/W
			[5]	-	-	278	K/W
			[6]	-	-	164	K/W
			[7]	-	-	179	K/W
			[8]	-	-	86	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	30	K/W

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per device							
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	245	K/W
			[2]	-	-	160	K/W
			[3]	-	-	171	K/W
			[4]	-	-	130	K/W
			[5]	-	-	202	K/W
			[6]	-	-	120	K/W
			[7]	-	-	130	K/W
			[8]	-	-	63	K/W

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- [6] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

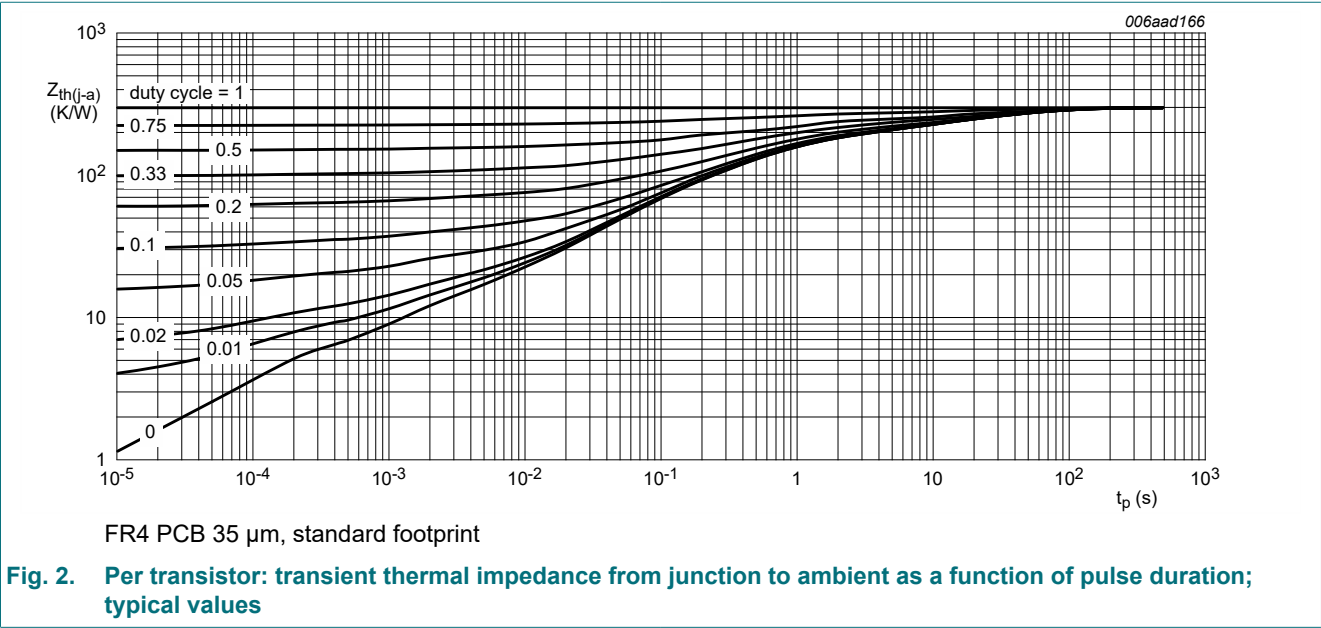
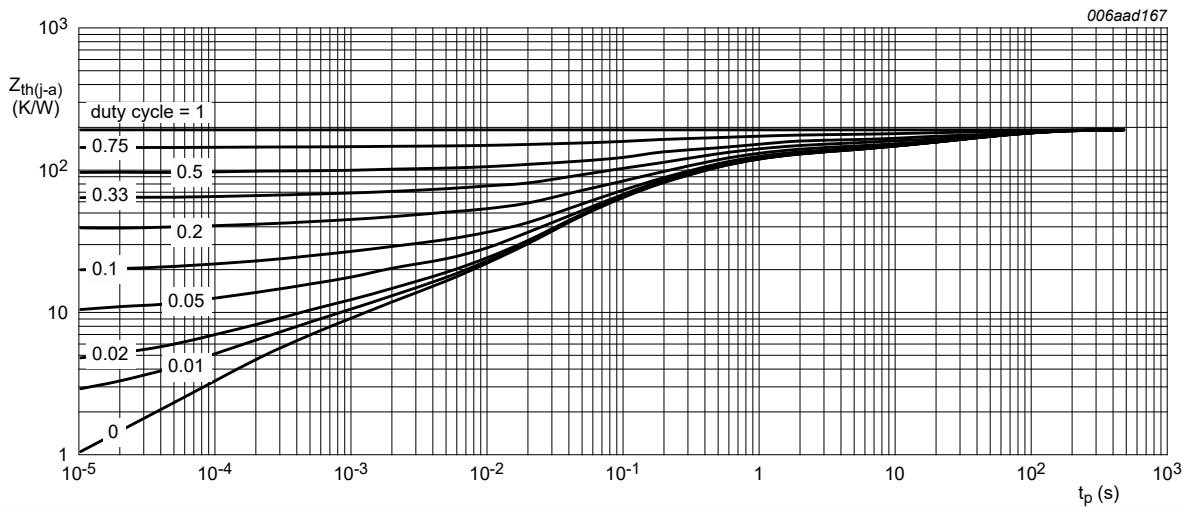
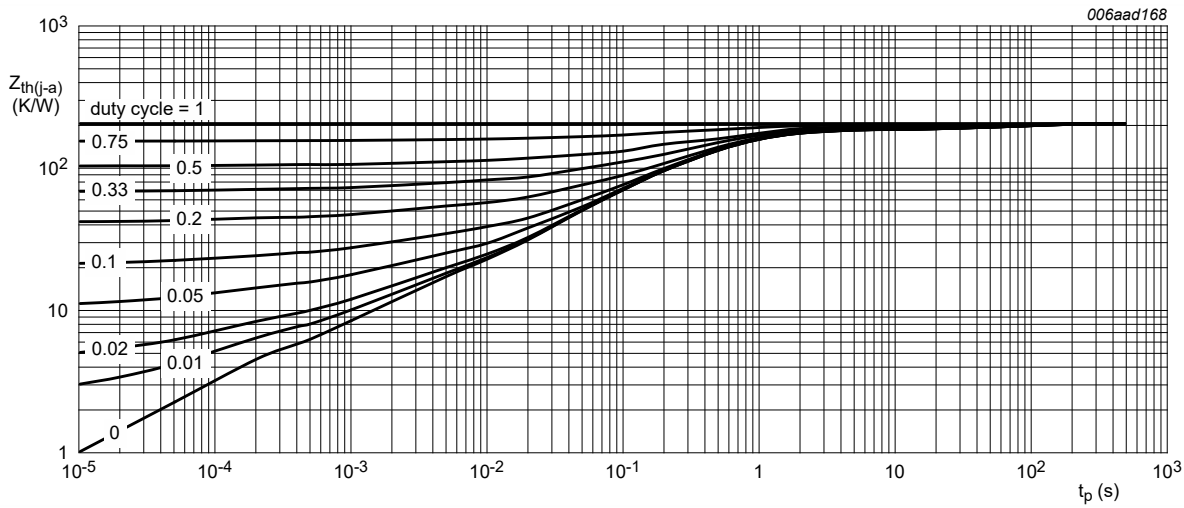


Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB 35  $\mu$ m, mounting pad for collector 1 cm<sup>2</sup>

Fig. 3. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



4-layer PCB 35  $\mu$ m, standard footprint

Fig. 4. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

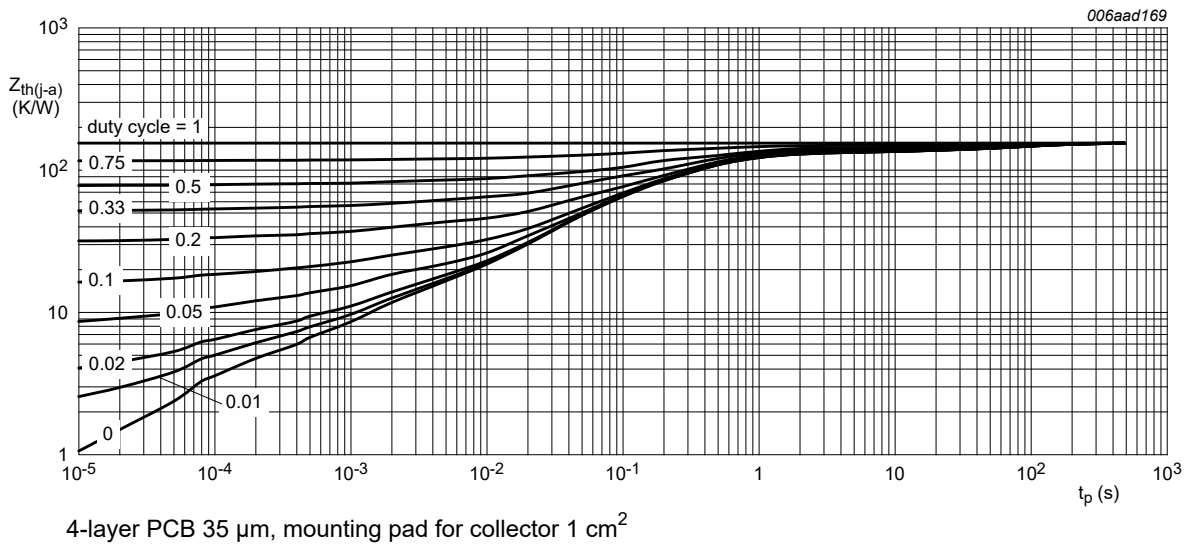


Fig. 5. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

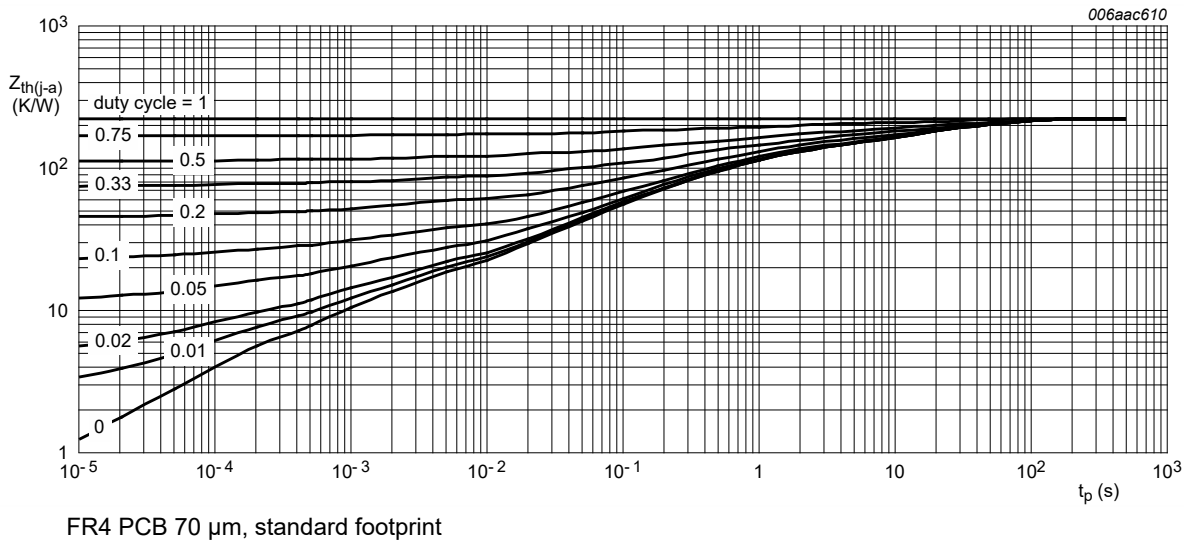
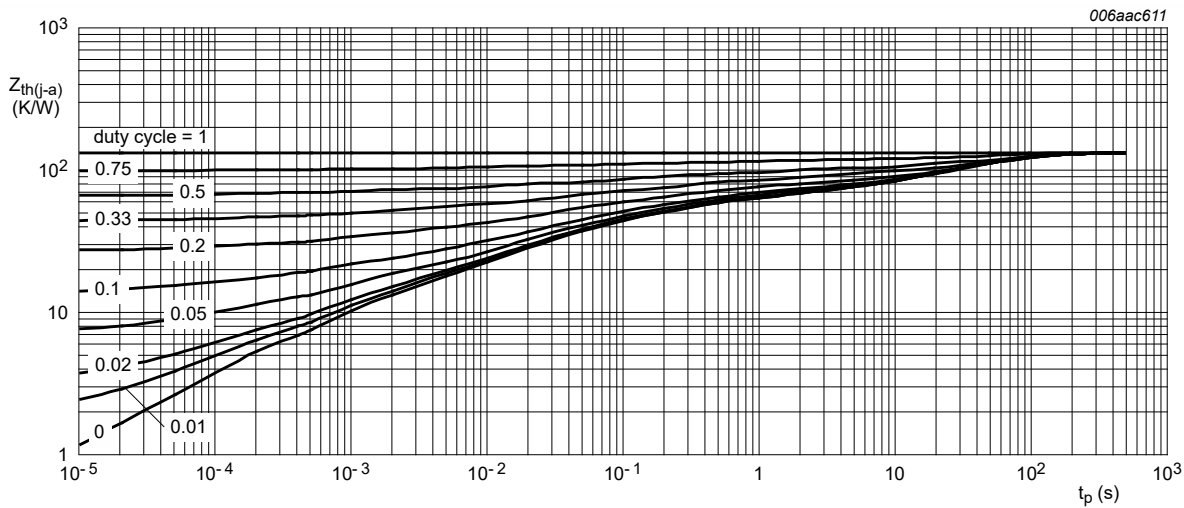
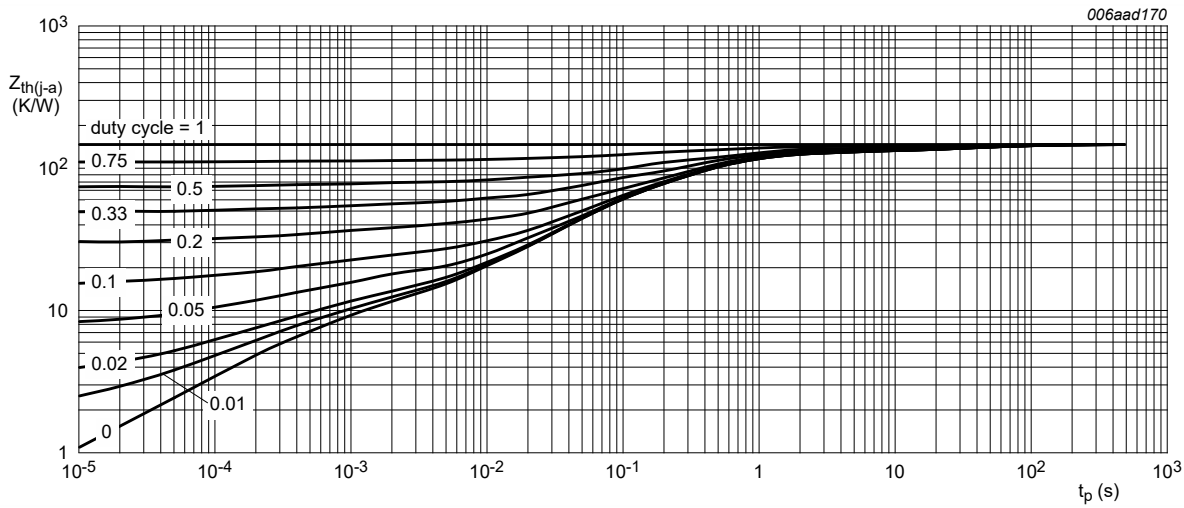


Fig. 6. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB 70  $\mu$ m, mounting pad for collector 1 cm<sup>2</sup>

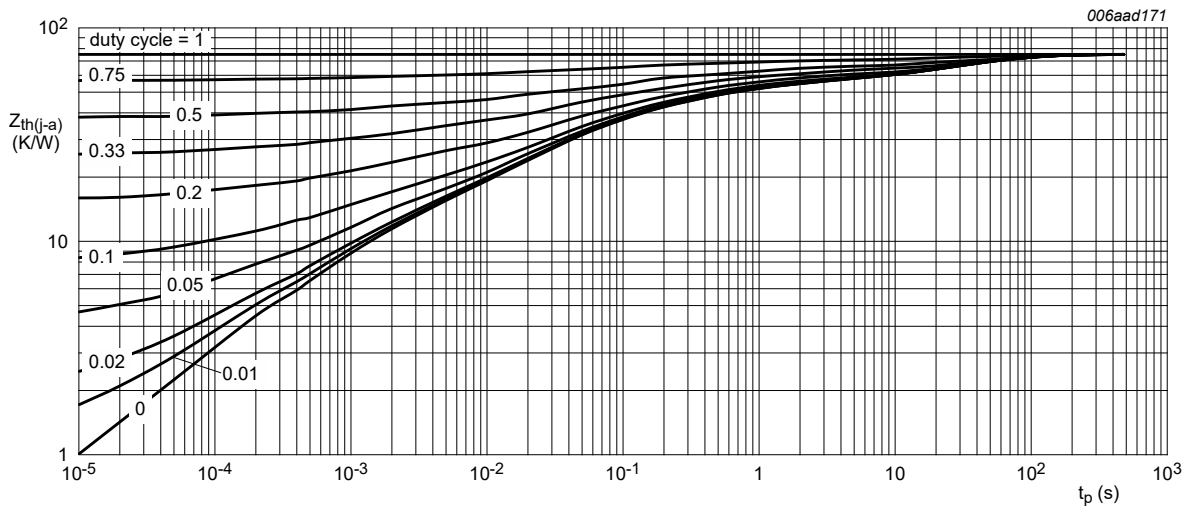
Fig. 7. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



4-layer PCB 70  $\mu$ m, standard footprint

Fig. 8. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values





4-layer PCB 70  $\mu\text{m}$ , mounting pad for collector 1  $\text{cm}^2$

**Fig. 9.** Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
TR1 (NPN)							
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
		V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	50	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 2 V; I <sub>C</sub> = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C		290	430	-	
		V <sub>CE</sub> = 2 V; I <sub>C</sub> = 500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C		150	220	-	
		V <sub>CE</sub> = 2 V; I <sub>C</sub> = 1 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C		70	110	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C		-	90	120	mV
		I <sub>C</sub> = 1 A; I <sub>B</sub> = 50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C		-	185	240	mV
		I <sub>C</sub> = 1 A; I <sub>B</sub> = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C		-	175	220	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = 0.5 A; I <sub>B</sub> = 50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C		-	-	240	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C		-	-	1	V
		I <sub>C</sub> = 1 A; I <sub>B</sub> = 50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C		-	-	1.1	V
		I <sub>C</sub> = 1 A; I <sub>B</sub> = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C		-	-	1.1	V
V <sub>BEon</sub>	base-emitter turn-on voltage	V <sub>CE</sub> = 2 V; I <sub>C</sub> = 0.5 A; t <sub>p</sub> ≤ 300 μs; pulsed; δ ≤ 0.02; T <sub>amb</sub> = 25 °C		-	-	0.9	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 10 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 25 mA; I <sub>Boff</sub> = -25 mA; T <sub>amb</sub> = 25 °C		-	15	-	ns
t <sub>r</sub>	rise time			-	90	-	ns
t <sub>on</sub>	turn-on time			-	105	-	ns
t <sub>s</sub>	storage time			-	410	-	ns
t <sub>f</sub>	fall time			-	130	-	ns
t <sub>off</sub>	turn-off time			-	540	-	ns
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 50 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C		90	175	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C		-	4	6	pF
TR2 (PNP)							
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = -48 V; I <sub>E</sub> = 0 A		-	-	-100	nA
		V <sub>CB</sub> = -48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A		-	-	-100	nA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	170	245	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	120	170	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -1 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	70	100	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-125	-180	mV
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-390	-550	mV
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-240	-340	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = -0.5 A; I <sub>B</sub> = -50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	360	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-1	V
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-1	V
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-1.1	V
V <sub>BEon</sub>	base-emitter turn-on voltage	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -0.5 A; t <sub>p</sub> ≤ 300 μs; pulsed; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-0.9	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -10 V; I <sub>C</sub> = -0.5 A; I <sub>Bon</sub> = -25 mA; I <sub>Boff</sub> = 25 mA; T <sub>amb</sub> = 25 °C	-	15	-	ns
t <sub>r</sub>	rise time		-	40	-	ns
t <sub>on</sub>	turn-on time		-	55	-	ns
t <sub>s</sub>	storage time		-	95	-	ns
t <sub>f</sub>	fall time		-	40	-	ns
t <sub>off</sub>	turn-off time		-	135	-	ns
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -50 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	65	125	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	9.5	13	pF

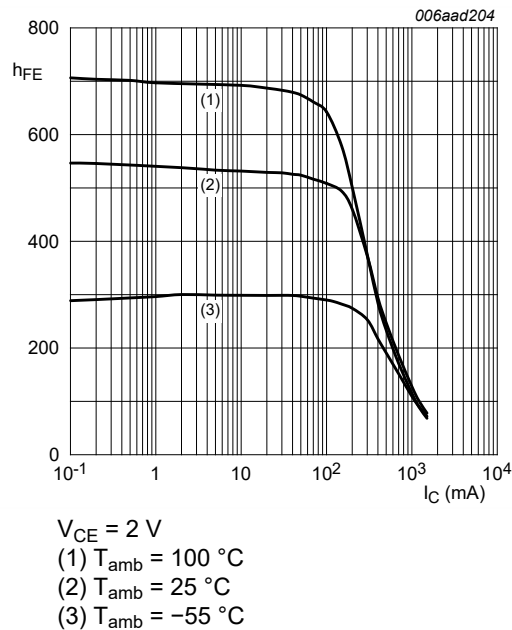


Fig. 10. TR1 (NPN): DC current gain as a function of collector current; typical values

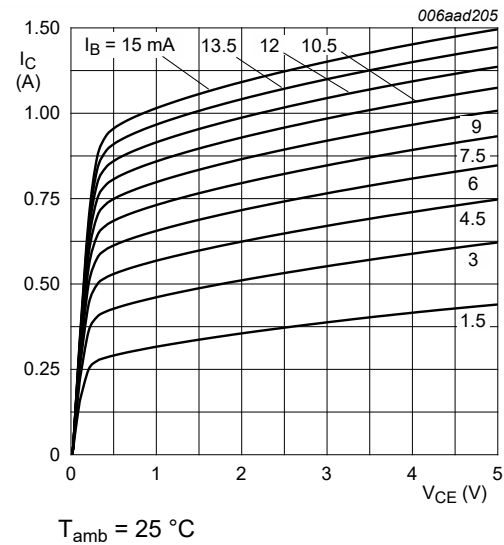


Fig. 11. TR1 (NPN): Collector current as a function of collector-emitter voltage; typical values

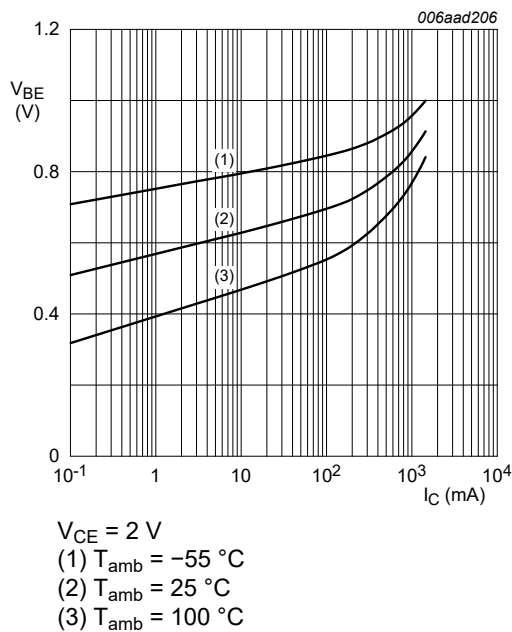


Fig. 12. TR1 (NPN): Base-emitter voltage as a function of collector current; typical values

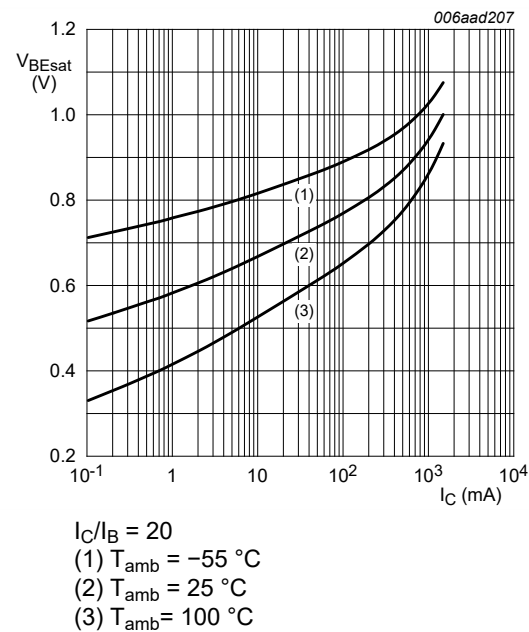


Fig. 13. TR1 (NPN): Base-emitter saturation voltage as a function of collector current; typical values

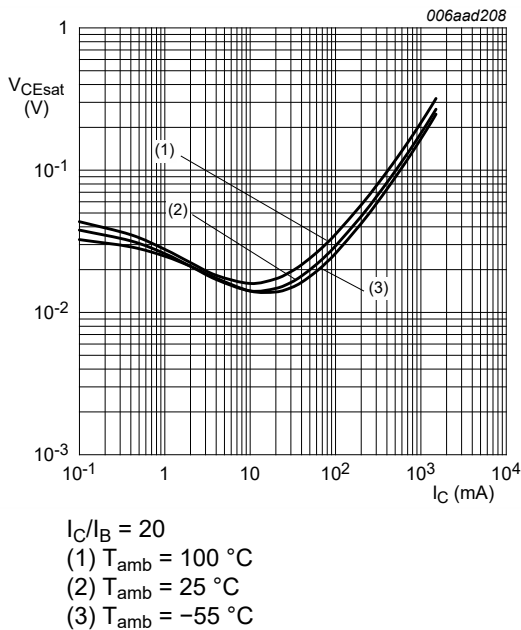


Fig. 14. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values

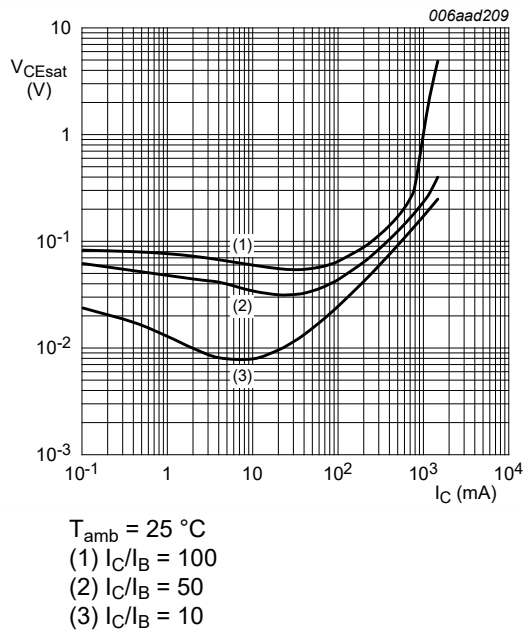


Fig. 15. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values

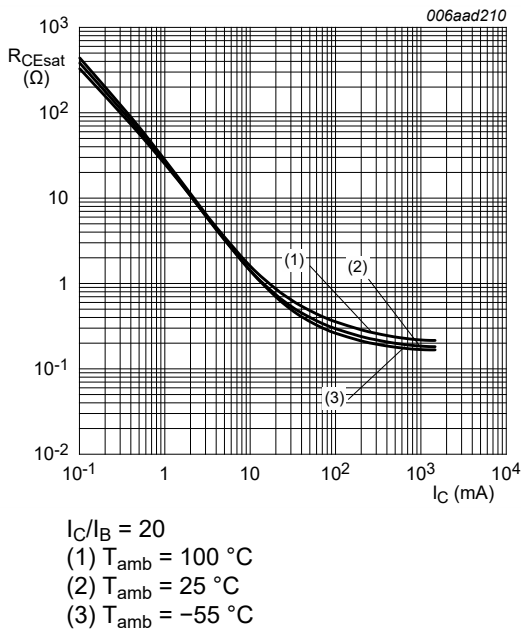


Fig. 16. TR1 (NPN): Collector-emitter saturation resistance as a function of collector current; typical values

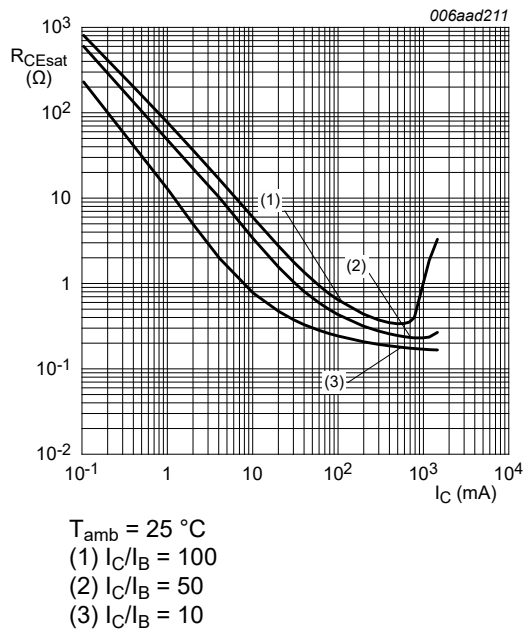


Fig. 17. TR1 (NPN): Collector-emitter saturation resistance as a function of collector current; typical values

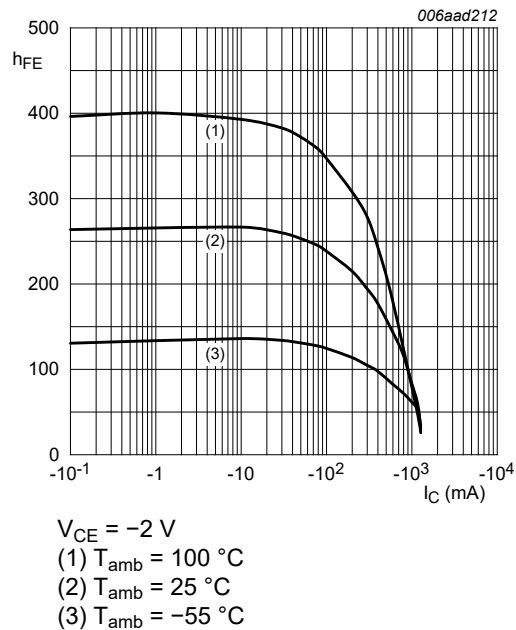


Fig. 18. TR2 (PNP): DC current gain as a function of collector current; typical values

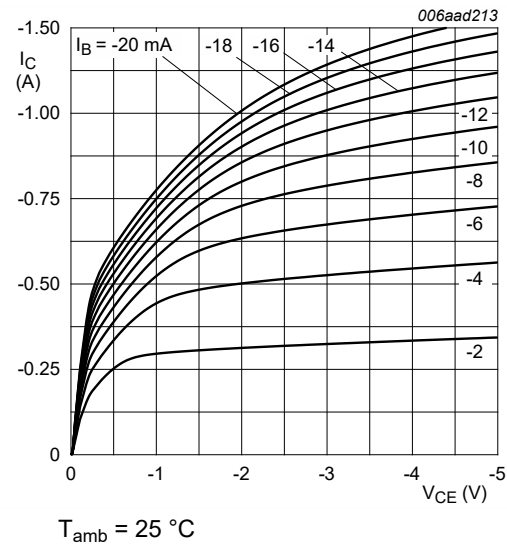


Fig. 19. TR2 (PNP): Collector current as a function of collector-emitter voltage; typical values

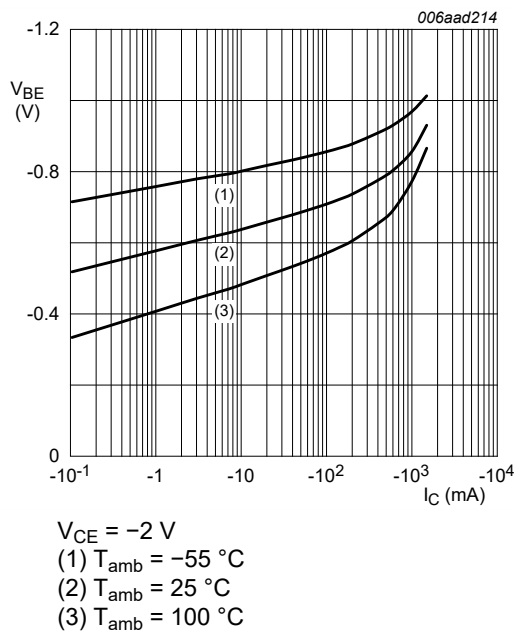


Fig. 20. TR2 (PNP): Base-emitter voltage as a function of collector current; typical values

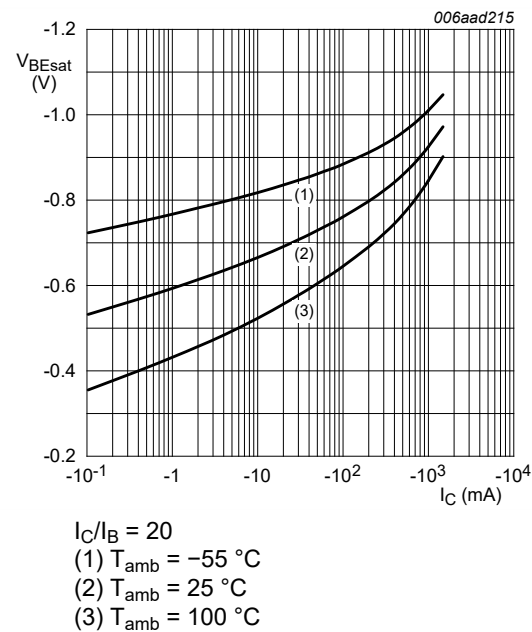


Fig. 21. TR2 (PNP): Base-emitter saturation voltage as a function of collector current; typical values

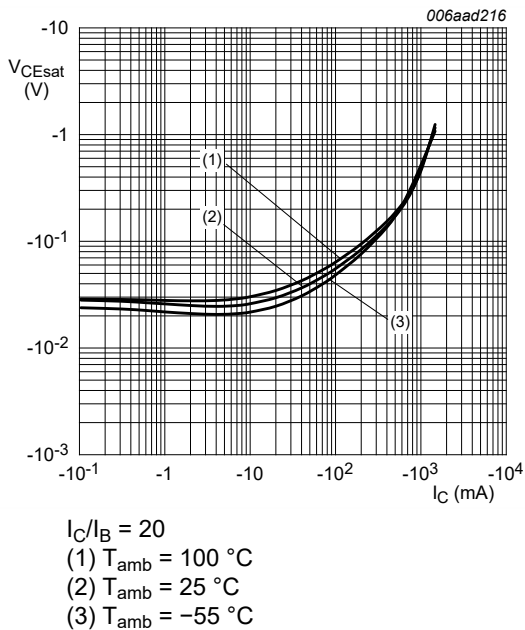


Fig. 22. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

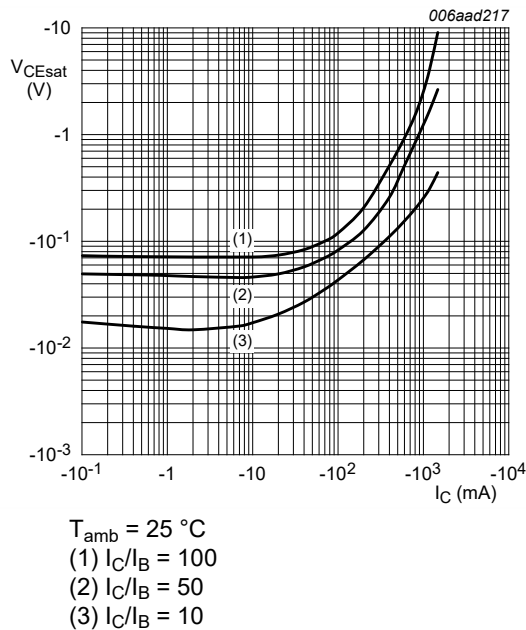


Fig. 23. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

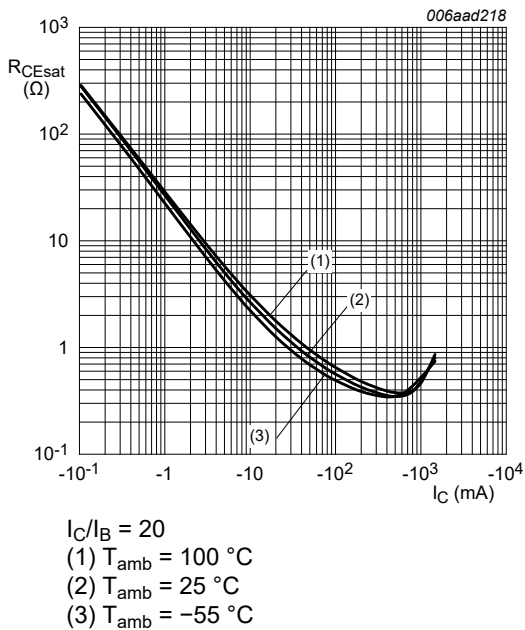


Fig. 24. TR2 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values

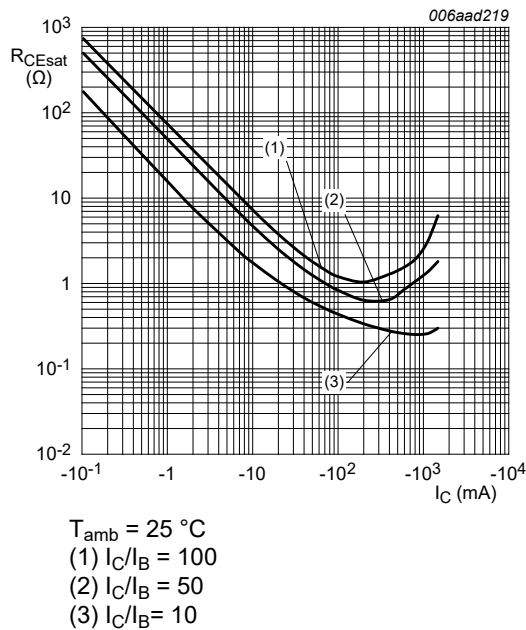


Fig. 25. TR2 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

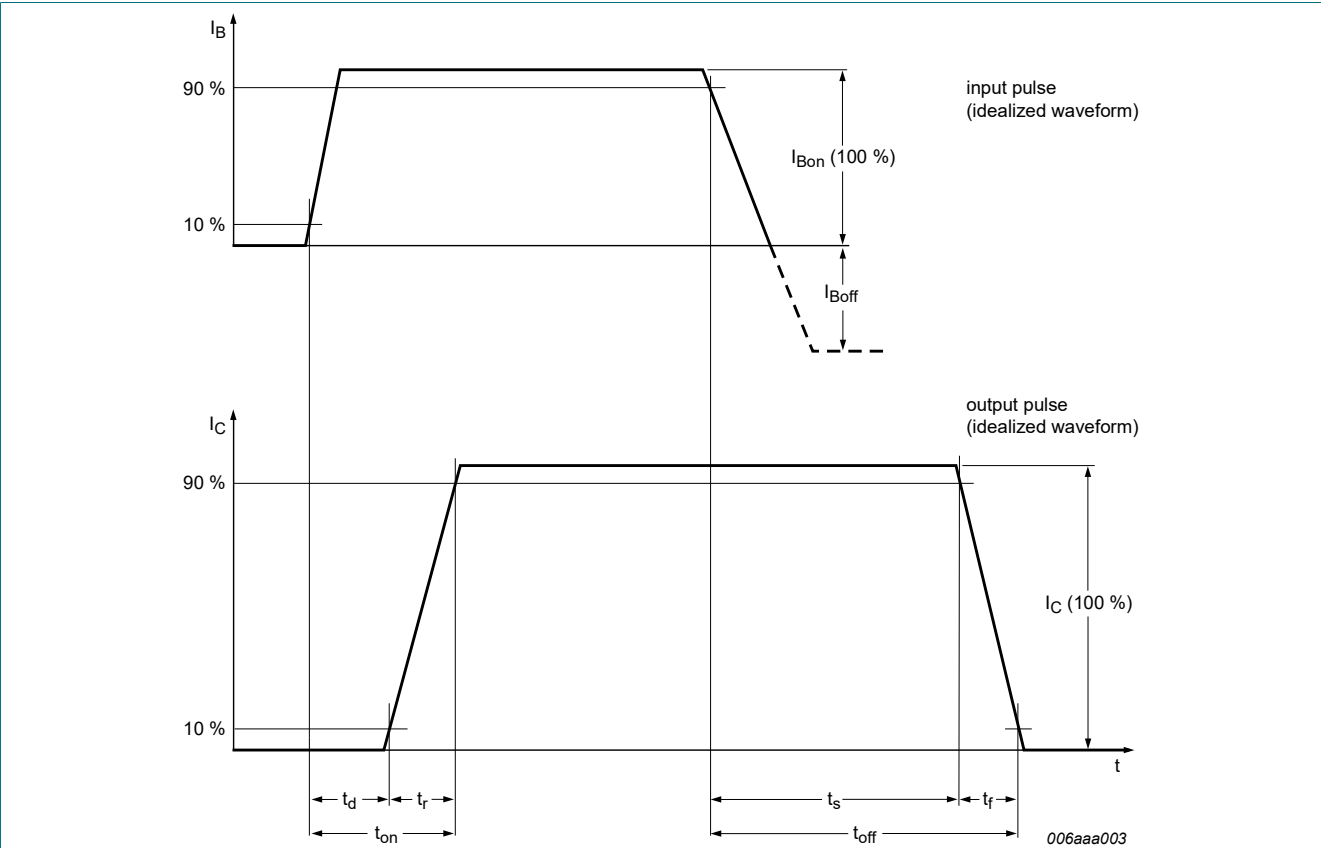


Fig. 26. TR1 (NPN): BISS transistor switching time definition

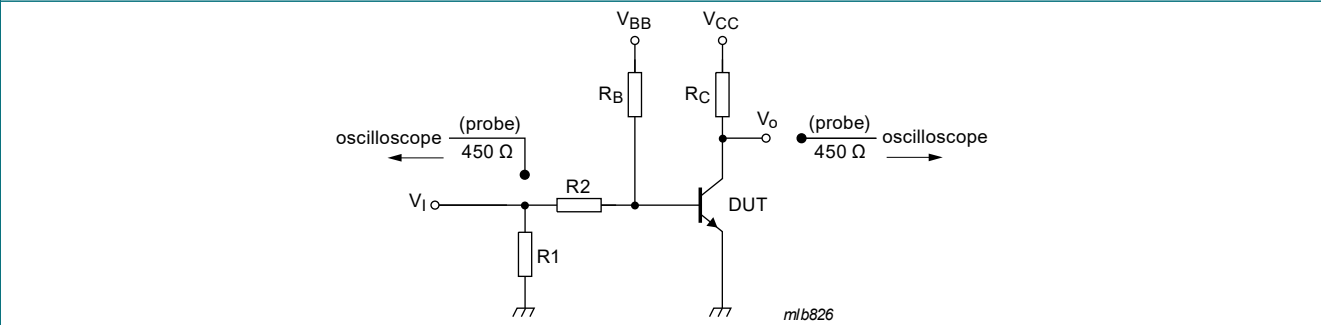


Fig. 27. TR1 (NPN): Test circuit for switching times



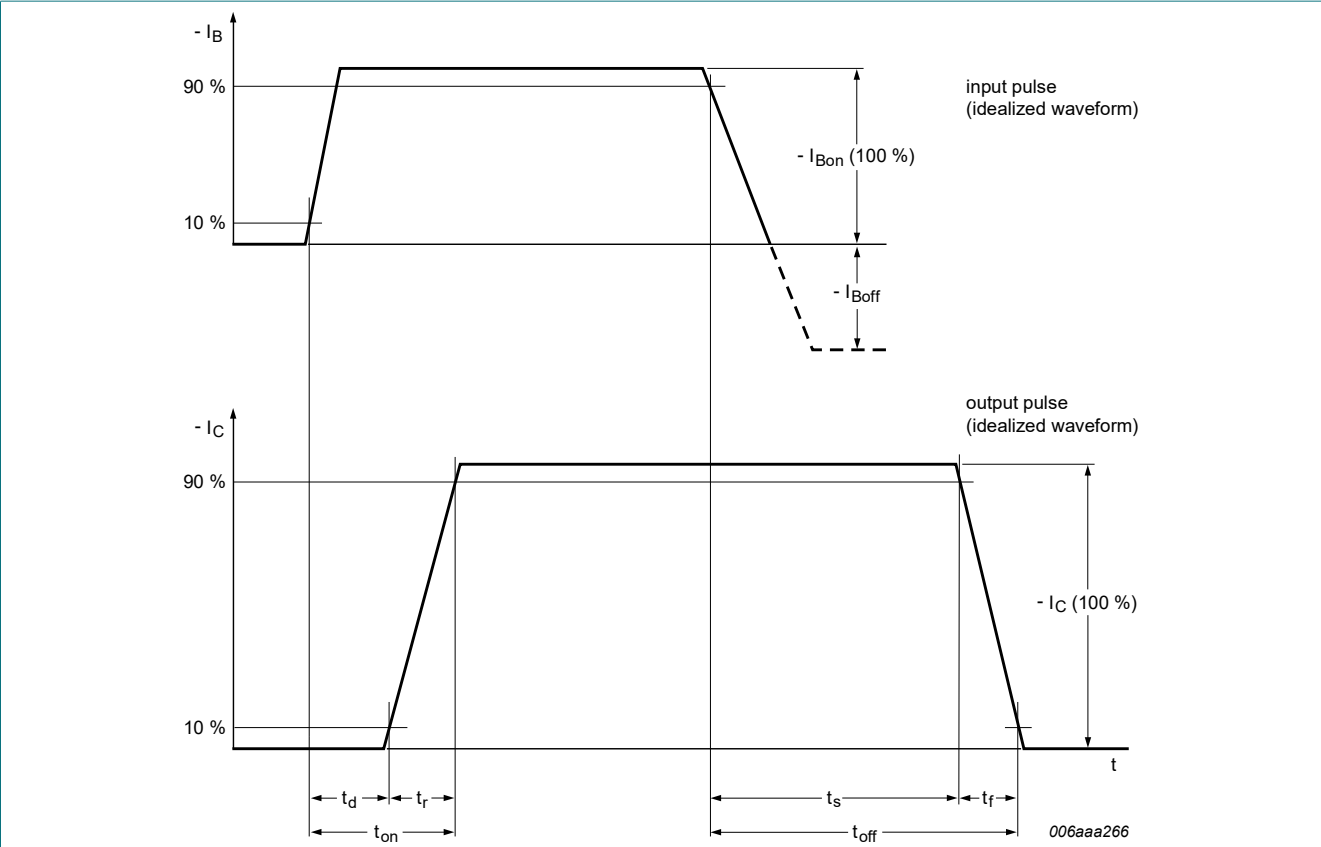


Fig. 28. TR2 (PNP): BISS transistor switching time definition

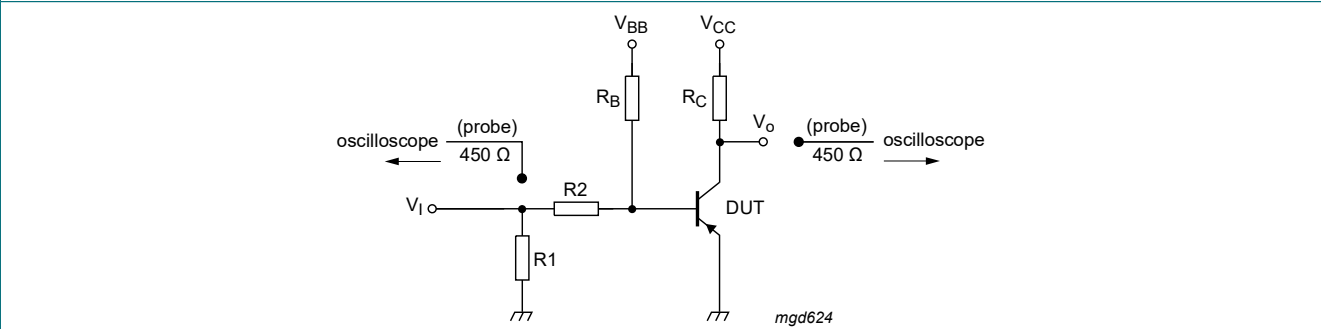
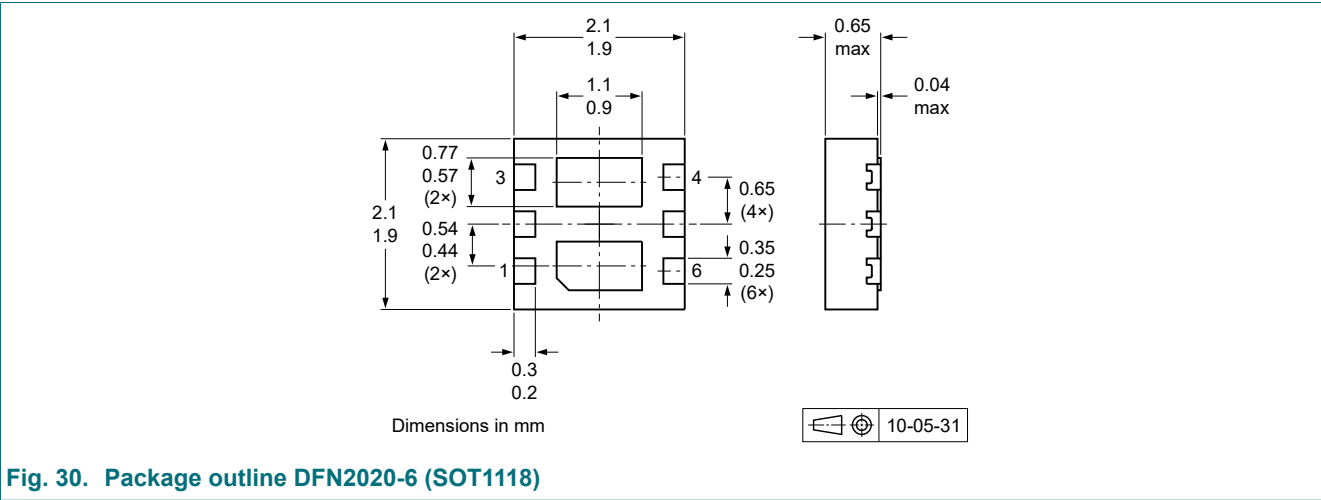
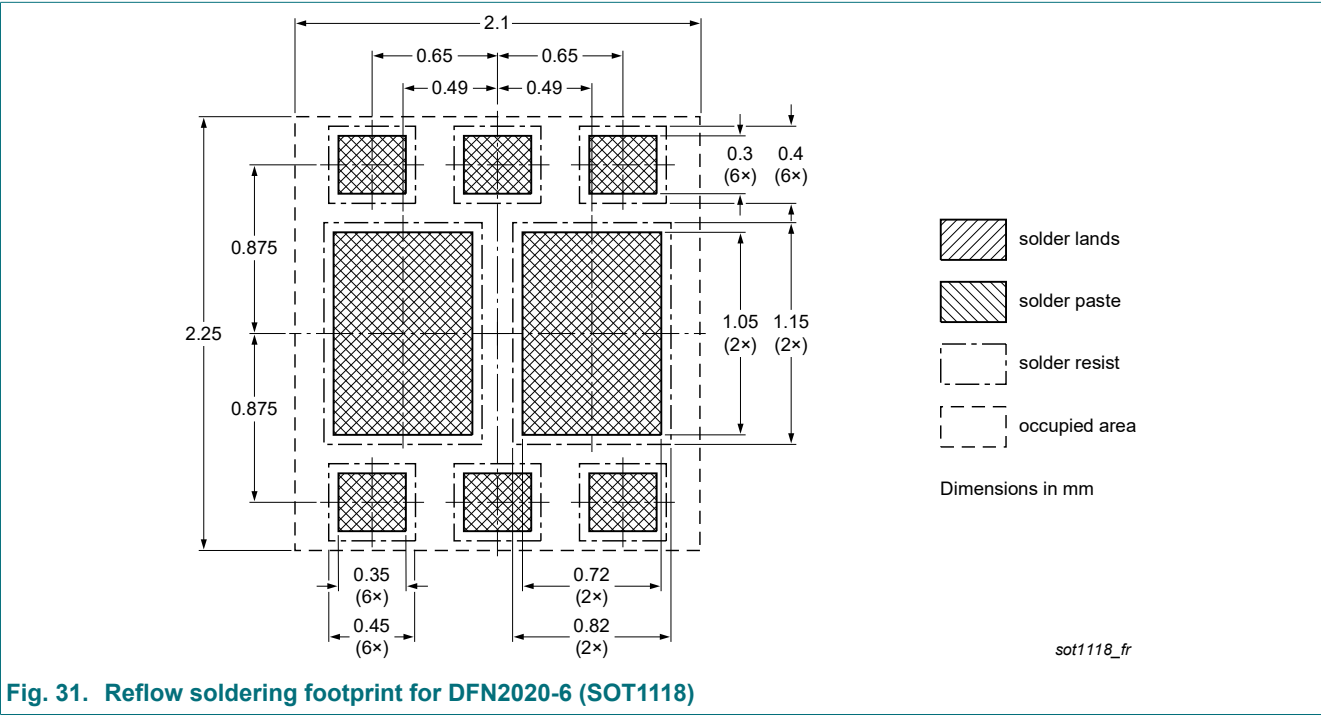


Fig. 29. TR2 (PNP): Test circuit for switching times

12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4160PANP v.3	20250930	Product data sheet	-	PBSS4160PANP v.2
Modifications:	<ul style="list-style-type: none"><li>Product(s) changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s).</li></ul>			
PBSS4160PANP v.2	20171220	Product data sheet	-	PBSS4160PANP v.1
PBSS4160PANP v.1	20130114	Product data sheet	-	-

## 15. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <https://www.nexperia.com>.

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